

# United States Patent and Trademark Office

UNITED STATES DEPARTMENT OF COMMERCE United States Patent and Trademark Office Address: COMMISSIONER FOR PATENTS P.O. Box 1450 Alexandria, Virginia 22313-1450 www.uspto.gov

APPLICATION NO.		FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
09/937,538		09/25/2001	Michihiro Mizuno	81839.0102	2057	
26021	7590	12/08/2003		EXAM	EXAMINER	
HOGAN & HARTSON L.L.P. 500 S. GRAND AVENUE				SIEFKE, SA	SIEFKE, SAMUEL P	
SUITE 1900				ART UNIT	PAPER NUMBER	
LOS ANGI	ELES, CA	90071-2611		1743		
				DATE MAILED: 12/08/2003		

Please find below and/or attached an Office communication concerning this application or proceeding.

		Applica	ation No.	Applicant(s)						
Office Action Summary			,538	MIZUNO, MICHIE	MIZUNO, MICHIHIRO					
			ner	Art Unit						
		1	P Siefke	1743						
	Th MAILING DATE of this communication appears on the cover shet with the correspondence address Period for Reply									
A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.  - Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.  - If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.  - If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.  - Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133).  - Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).  Status										
	Responsive to communication(s) file	ed on .								
·	•	2b)⊠ This action is	non-final.	•						
- ,—	Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213.									
Disposition of Claims										
4)	Claim(s) <u>1-18</u> is/are pending in the application.									
	4a) Of the above claim(s) is/are withdrawn from consideration.									
5)□	Claim(s) is/are allowed.									
6)⊠	Claim(s) <u>1 and 7</u> is/are rejected.									
•	Claim(s) <u>2-6 and 8-18</u> is/are objected to.									
8)∐	8) Claim(s) are subject to restriction and/or election requirement.									
Applicati	ion Papers									
•	The specification is objected to by the		_							
10) The drawing(s) filed on is/are: a) □ accepted or b) □ objected to by the Examiner.										
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).										
	Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).									
11) The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.										
-	Priority under 35 U.S.C. §§ 119 and 120									
<ul> <li>12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).</li> <li>a) All b) Some * c) None of:</li> <li>1. Certified copies of the priority documents have been received.</li> <li>2. Certified copies of the priority documents have been received in Application No.</li> <li>3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).</li> <li>* See the attached detailed Office action for a list of the certified copies not received.</li> <li>13) Acknowledgment is made of a claim for domestic priority under 35 U.S.C. § 119(e) (to a provisional application) since a specific reference was included in the first sentence of the specification or in an Application Data Sheet.</li> <li>37 CFR 1.78.</li> <li>a) The translation of the foreign language provisional application has been received.</li> <li>14) Acknowledgment is made of a claim for domestic priority under 35 U.S.C. §§ 120 and/or 121 since a specific reference was included in the first sentence of the specification or in an Application Data Sheet. 37 CFR 1.78.</li> </ul>										
Attachmen	•		_							
2) Notic	ce of References Cited (PTO-892) ce of Draftsperson's Patent Drawing Review (I mation Disclosure Statement(s) (PTO-1449) F			Summary (PTO-413) Paper No Informal Patent Application (PT						

Application/Control Number: 09/937,538

Art Unit: 1743

#### **DETAILED ACTION**

### Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States

Claim 1 is rejected under 35 U.S.C. 102(b) as being anticipated by JP 409015174.

JP '174 discloses a method for chemical analysis of a surface of a silicon wafer. First the pressure in the vessel is reduced by a vacuum pump and a silicon wafer is heated by a hot plate (2) to condense a chemical by evaporation. Then a very small quantity of recovery solution (sulfuric acid or fluoric acid) is dropped onto the surface of the wafer (3). Scanning is made all over the surface of the wafer so as to dissolve and recover an evaporation residue, and impurities in the recovery solution are then analyzed (abstract). The abstract refers to the heating temperature being relatively low because of the high sulfuric acid boiling point and also heating under pressurized circumstances requires a lower temperature to evaporate a substance. It is inherent that if one did not use a vacuum then the temperature required to heat the wafer in order for the chemicals in the wafer to come to the surface would be significantly higher, but under the boiling point of sulfuric acid which is 280° C.

Application/Control Number: 09/937,538

Art Unit: 1743

## Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

The factual inquiries set forth in *Graham* v. *John Deere Co.*, 383 U.S. 1, 148 USPQ 459 (1966), that are applied for establishing a background for determining obviousness under 35 U.S.C. 103(a) are summarized as follows:

- 1. Determining the scope and contents of the prior art.
- 2. Ascertaining the differences between the prior art and the claims at issue.
- 3. Resolving the level of ordinary skill in the pertinent art.
- 4. Considering objective evidence present in the application indicating obviousness or nonobviousness.

Claims **7** are rejected under 35 U.S.C. 103(a) as being unpatentable over JP 409015174 in view of Watanabe (USPN 6,444,010).

JP '174 discloses a method for chemical analysis of a surface of a silicon wafer. First the pressure in the vessel is reduced by a vacuum pump and a silicon wafer is heated by a hot plate (2) to condense a chemical by evaporation. Then a very small quantity of recovery solution (sulfuric acid or fluoric acid) is dropped onto the surface of the wafer (3). Scanning is made all over the surface of the wafer so as to dissolve and recover an evaporation residue, and impurities in the recovery solution are then analyzed (abstract).

JP '174 does not teach the impurity to be recovered is Cu.

Application/Control Number: 09/937,538

Art Unit: 1743

Watanabe teaches an impurity recovery liquid and method for recovering an impurity. The impurity of interest includes Cu element. It would have been obvious to recovery the Cu impurity because copper is a common impurity in silicon wafers.

### Allowable Subject Matter

Claims 2-6, 8-18 are objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims. Claim 2 would be allowable because the prior are does not teach or fairly suggest putting another uncontaminated wafer on the concentrated sulfuric acid on the silicon wafer to hold the concentrated sulfuric acid between the wafers, and subjecting the whole of the wafers in that state to a heat treatment (specifically 100°C to 270°C). Claim 4 would be allowable because the prior are does not teach or fairly suggest neutralizing the concentrated sulfuric acid on the silicon wafer by exposing it to an ammonia gas atmosphere.

#### Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Samuel P Siefke whose telephone number is 703-306-0093. The examiner can normally be reached on M-F 7:00am-5:00pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Jill A. Warden can be reached on 703-308-4037. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9311.

Application/Control Number: 09/937,538 Page 5

Art Unit: 1743

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is 703-308-0661.

Sam P. Siefke

November 25, 2003